

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A semiconductor device having a self-aligned contact hole, the device comprising:

a substrate;

a first conductor structure and a second conductor structure formed on the substrate;

an insulator structure formed on the first and second conductor structure and on the substrate except over the substrate in a region between the first and second conductor structures; and

C' sidewall spacers, each sidewall spacer being formed to abut against both a side of the first or second conductor structures and a side of the insulator structure such that a vertical portion of each sidewall spacer abuts the conductor structures, the sidewall spacers manifesting the self-aligned contact hole in the region between the first and second conductor structures, wherein the self-aligned contact hole does not overlap any part of the first and second conductor structures.

2. (Original) The semiconductor device of claim 1, wherein the first and second conductor structures are first and second gate structures, respectively.

3. (Original) The semiconductor device of claim 1, wherein the first and second conductor structures comprise:

- a gate oxide layer formed on the substrate;
- a conductive layer formed on the gate oxide layer; and
- a gate cap insulating layer formed on the conductive layer.

4. (Original) The semiconductor device of claim 1, further comprising:
a contact plug formed in the self-aligned contact hole.

5. (Currently Amended) An unsymmetrical semiconductor device using a self-aligned contact hole, the device comprising:

- a substrate having impurity regions formed therein;
- a first conductor structure and a second conductor structure formed on the substrate;

first sidewall spacers, each first sidewall spacer being formed to abut against both a side of the first or second conductor structures and a side of an insulator structure such that a vertical portion of each sidewall spacer abuts the conductor structures, the first sidewall spacers manifesting the self-aligned contact hole in the region between the first and second conductor structures, wherein the self-aligned contact hole does not overlap any part of the first and second conductor structures; and

second sidewall spacers formed on sides of the first and second conductor structures opposite of the self-aligned contact hole.

6. (Original) The unsymmetrical semiconductor device of claim 5, wherein the ion concentration of a first impurity region is different than the ion concentration of a second impurity region.

7. (Currently Amended) The unsymmetrical semiconductor device of claim ~~5~~ 6, further comprising:

a contact plug formed in the self-aligned contact hole, the contact plug being in contact with the first sidewall spacers and the first impurity region.

8. (Original) The unsymmetrical semiconductor device of claim 7, wherein the contact plug is also in contact with a bit line.

9. (Original) The unsymmetrical semiconductor device of claim 7, wherein the contact plug is not disposed directly above the first and second conductor structures.
